

ALTERNATIVE TO PTO/SB/08a/b (07-05)

Substitute for form 1449/PTO		Complete if Known			
Sub	Sulute for form 1449/PT	U		Application Number	10/772,585
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	February 6, 2004
				First Named Inventor	Tetsuro Asano
		U .,	WI LIOANI	Art Unit	2813
	(Use as many	sheets as	necessary)	Examiner Name	Laura M. Schillinger
Sheet	1	of	1	Attorney Docket Number	492322017600

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	

FOREIGN PATENT DOCUMENTS								
Examiner Initiats*	Cite No.1	Foreign Patent Document	Publication	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
		Country Code ³ -Number ⁴ -Kind Code ³ (if known)	Date MM-DD-YYYY			T⁰		
De	1.	JP-2-162744	06-22-1990			1		
_ `	2.	WO-97/45877	04-12-1997		Translation of	Т		
M		l			abstract only	L		

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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Τ²		
Kler	3.	MIYAWAKI, Yasuo et al. (1986) "Ion-Implanted Low Noise Dual-Gate GaAs MESFET," Sanyo Technical Review 18(2), pp. 76-84			

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